

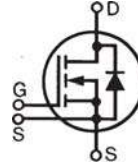
HiPerFET™ Power MOSFET

Single MOSFET Die

IXFN 24N100
IXFN 23N100

V_{DSS}	I_{D25}	$R_{DS(on)}$
1000 V	24 A	0.39 Ω
1000 V	23 A	0.43 Ω

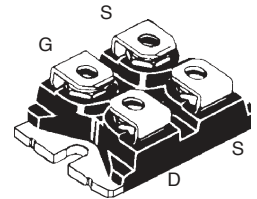
$t_{rr} \leq 250$ ns



Symbol Test Conditions		Maximum Ratings	
V_{DSS}	$T_J = 25^{\circ}\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^{\circ}\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^{\circ}\text{C}$	24N100: 24 23N100: 23	A
I_{DM}	$T_C = 25^{\circ}\text{C}$; Note 1	24N100: 96 23N100: 92	A
I_{AR}	$T_C = 25^{\circ}\text{C}$	24	A
E_{AR}	$T_C = 25^{\circ}\text{C}$	60	mJ
E_{AS}	$T_C = 25^{\circ}\text{C}$	3	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/ μs , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^{\circ}\text{C}$, $R_G = 2$ Ω	5	V/ns
P_D	$T_C = 25^{\circ}\text{C}$	600	W
T_J		-55 ... +150	$^{\circ}\text{C}$
T_{JM}		150	$^{\circ}\text{C}$
T_{stg}		-55 ... +150	$^{\circ}\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^{\circ}\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1$ min $I_{ISOL} \leq 1$ mA $t = 1$ s	2500 3000	V~ V~
M_d	Mounting torque Terminal connection torque	1.5/13 Nm/lb.in. 1.5/13 Nm/lb.in.	
Weight		30	g

miniBLOC, SOT-227 B (IXFN)

E153432



G = Gate
S = Source
D = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions ($T_J = 25^{\circ}\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 3$ mA	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8$ mA	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 20$ V, $V_{DS} = 0$ V			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0$ V	$T_J = 25^{\circ}\text{C}$ $T_J = 125^{\circ}\text{C}$		100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 I_{D25}$ Note 2	23N100 24N100		0.43 Ω 0.39 Ω

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \ddot{I}_{D25}$, Note 2	15	22	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		7000	pF
C_{oss}			750	pF
C_{rss}			260	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \ddot{I}_{DSS}, I_D = 0.5 \ddot{I}_{D25}$ $R_G = 1\ \Omega$ (External),		35	ns
t_r			35	ns
$t_{d(off)}$			75	ns
t_f			21	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \ddot{I}_{DSS}, I_D = 0.5 \ddot{I}_{D25}$		250	nC
Q_{gs}			55	nC
Q_{gd}			135	nC
R_{thJC}			0.21	K/W
R_{thCK}		0.05		K/W

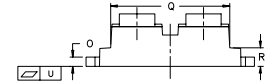
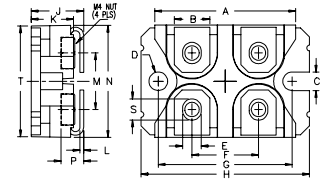
Source-Drain Diode

($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
I_S	$V_{GS} = 0$	24N100 23N100		24 23	A A
I_{SM}	Repetitive; pulse width limited by T_{JM}	24N100 23N100		96 92	A A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5	V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		1.0	250	ns
Q_{RM}			8		μC
I_{RM}					A

- Notes: 1. Pulse width limited by T_{JM} .
2. Pulse test, $t \leq 300\text{ ms}$, duty cycle $d \leq 2\%$.

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

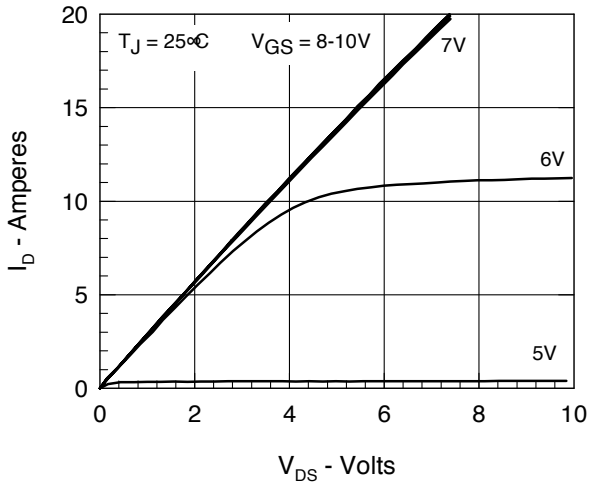


Figure 1. Output Characteristics at 25°C

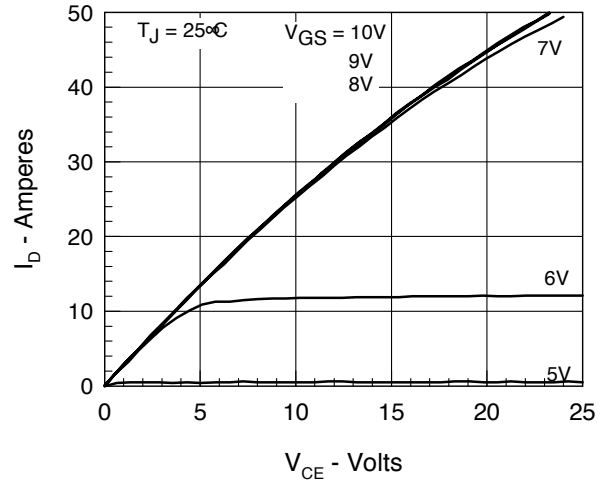


Figure 2. Extended Output Characteristics at 125°C

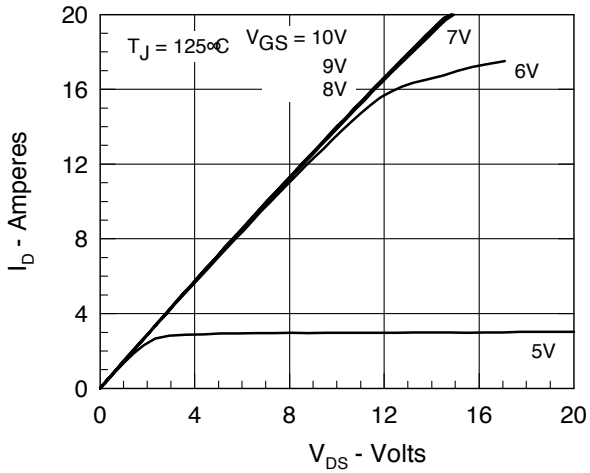


Figure 3. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. I_D

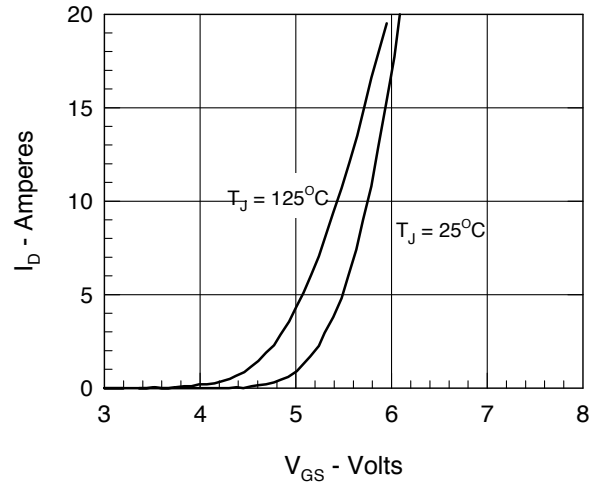


Figure 4. Admittance Curves

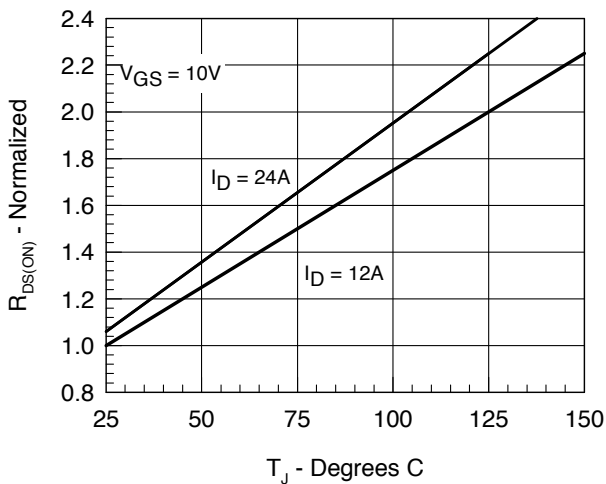


Figure 5. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. T_J

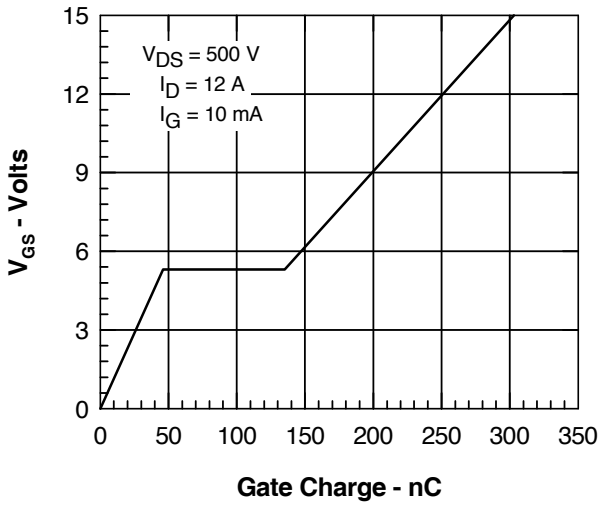


Figure 6. Gate Charge

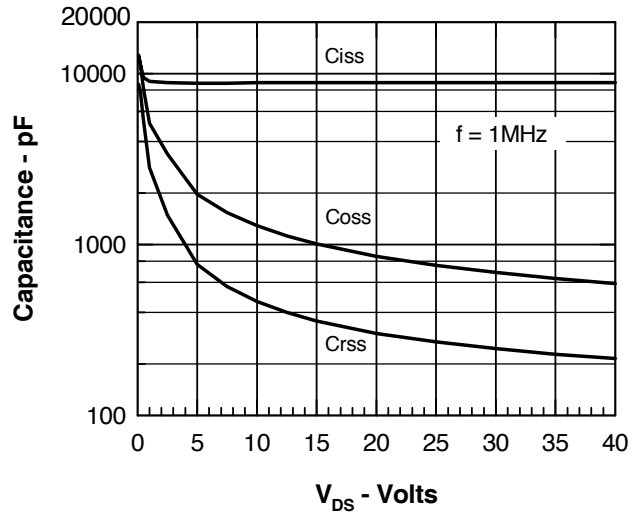


Figure 7. Capacitance Curves

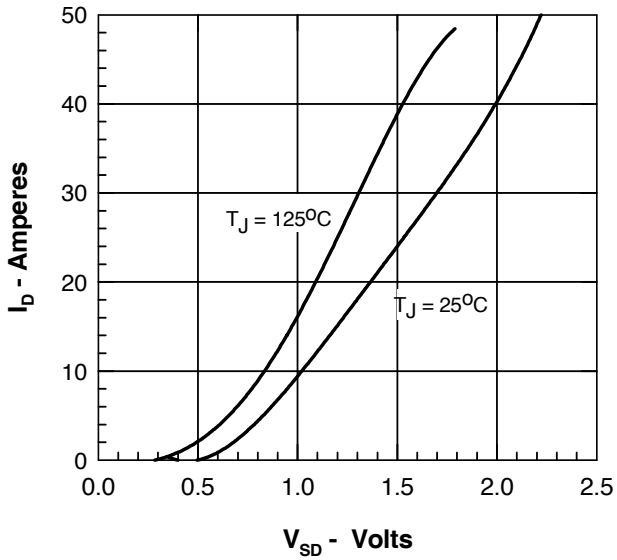


Figure 8. Forward Voltage Drop of the Intrinsic Diode

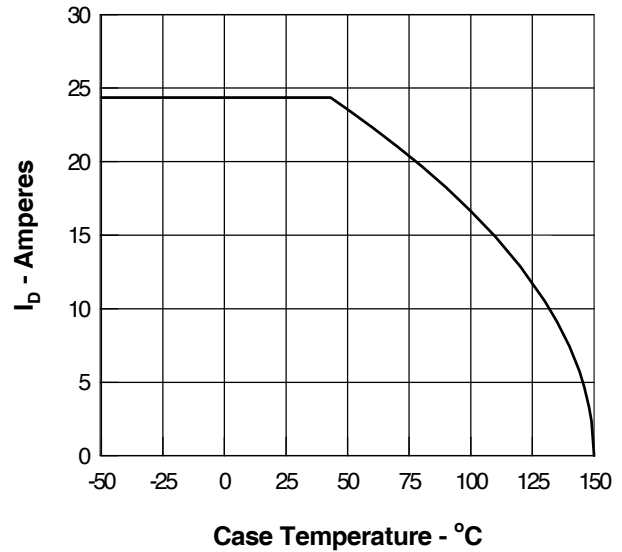


Figure 9. Drain Current vs. Case Temperature

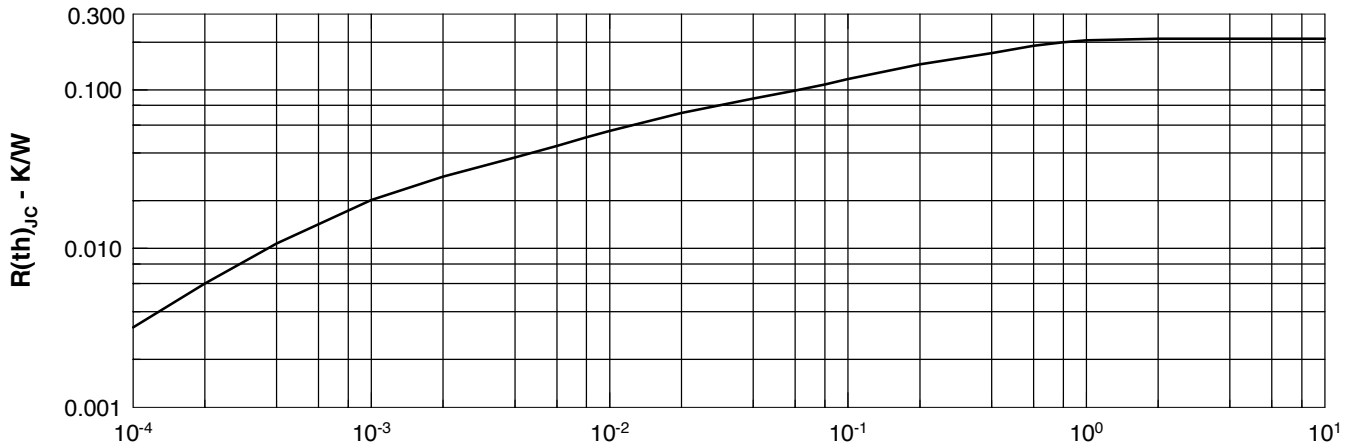


Figure 10. Transient Thermal Resistance